Degradation effects in TIBr single crystals under prolonged bias voltage



(Thermo) Electro aging

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TIBr properties



- high atomic numbers Z: 81+35
 stopping power
- density (7.56 g/cm3)
 => compact device
- bandgap (2.68 eV) => room temperature
- inter-pixel resistance ~500 G Ω (gap 100 μ m, 50V)
 - => 2D-array detector*
- optical transparency: $440nm 50\mu m =>$ scintillation spectroscopy

*Owens et al., Nucl. Instr. and Meth. A 531, 18 (2004)



V. Kozlov, et. al., Nucl. Instr. and Meth. A 531, 165 (2004).

Hardness (Knoop: 12 kg / mm²) => Manufacturing process

Material problems

TIBr – toxic compound

Instability of electrical properties



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Height pulse spectra

¹⁰⁹Cd source at 100V

time, min	0	10	130			
Relative peak position	1	0.7	0.36			
K Hitomi et al. IEEE Transactions on Nuclear Science 49(5 Pt 2) 2526 (2002)						

"Diode" breakdown



Degradation of photoconductivity

Ionic conductivity => channel structures J. Vaitkus, et al., Nucl. Instr. and Meth. A531 192 (2004)

Tl⁺ electro-diffusion => polarisation phenomena J. Vaitkus, et. al., Nucl. Instr. and Meth. A546(1-2), 188 (2005)

Sample preparation

X-ray rocking curves





FWHM

- Source 2.8°
- Annealing 1.5°

Slice formation



Size: 4.22 * 4.19 * 1.55 mm³ Ti electrode: 14 mm² * ~40 nm

I-V sweeps



jW1: 0V => +200V+ Standby ~1hjW2: +200V => -200V+ Standby ~1hjW3: -200V => +200VConductivity, t=23.8°C

•Max: 1.18E-09 [ohm.cm]⁻¹ •Min: 1.61E-10 [ohm.cm]⁻¹



Current-time characteristics

"Sweep" mode

Standby mode



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A9ElectroAging20deg.JPG





4, 20, 40, 60 and 80°C

Voltage range

0 - +200 V

Light pulses, 440 nm 3.0µ 200 V 2.5µ 2.0µ Current, A 100 V 1.5µ 1.0µ 50 V 25 V 500.0n 10 V 80°C 0.0 -50 Ó 50 100 150 200 250 300 350 400 450 Time, s

Prolonged aging

=> Electrode process?

SEM-EDS Measurements

Positive Ti-electrode



Under (+) Ti



Material of slit on (+) electrode



IWORID-8, Pisa, Italy, 2006



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Negative Ti-electrode



Under (-) Ti



Negative Ti surface aging



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Negative Ti surface degradationafter electro aging and+ 2 weeks, laboratory conditions



XRD & EDS results



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XRD: degradation of negative electrode

XRD: Negative & Positive Sides

Electrodes:

Negative & Positive

Atomic%	Standard	on	under	on	under
Element	slit	(+) Ti	(+)Ti	(-) Ti	(-) Ti
С	50.75	41.51	44.37	40.4	40.42
0	9.52	18.99	14.02	30.60	24.4
Br	20.38	10.65	21.83	2.96	11.85
TI	17.84	9.45	18.19	15.4	23.33
Ti	0.97	18.76	0.11	10.16	
Pb*	0.16	0.08	0.19	0.21	
Cl*	0.22	0.13	0.21		
W*	0.15	0.07	0.15	0.2	
Si		0.38	0.74		
Ag			0.19		
Ta*				0.07	
Co*	0.01				
Hal / TI	1.15	1.14	1.21	0.19	0.51

EDS: Composition

Max Min

Elements added by the fitting program

(-) side: Tl and O - max

Hal/Tl ratio – min

(+) **side**: Br and Ti -max.



Conclusions



- TI⁺ ionic current
 - => polarisation effects & degradation
 - => TIBr room temperature detector myth?
- Role of material quality and purity?
- Could be the electro-aging used for purification?





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• Thank You!